

1201.63407

PATENT APPLICATION

#14/Response
8/27/02
AdIN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re U.S. Patent Application

Applicant: Nayfeh et al.

Serial No. 09/496,506

Filed: February 2, 2000

For: SILICON NANOPARTICLE
FIELD EFFECT TRANSISTOR
AND TRANSISTOR MEMORY
DEVICE

Art Unit: 2811

Examiner: Crane, S.

) I hereby certify that this paper is being facsimile
) transmitted to the U.S. Patent and Trademark Office on
) this date.) Aug 26, 2002 As B R
) Date Registration No. 43,874
) ptofax.wcm
) Appr. April 11, 2000 Attorney for ApplicantRESPONSE B

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AUG 26 2002

TECHNOLOGY CENTER 2800

Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

In response to the Office Action mailed June 4, 2002, which has been made final, please consider the following remarks.

REMARKS

Claim 4 stands rejected under 35 U.S.C. § 112, second paragraph, as being indefinite. Particularly, the Examiner finds the term "energy spacing" unclear. Applicants respectfully traverse the rejection. The Office Action states that "the claim says that the